

U.S. Patent Application Serial No. 10/049,615
Amendment dated August 12, 2003
Reply to OA of March 20, 2003

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended): A ferromagnetic p-type single-crystal zinc oxide material including a ~~transition metal element consisting of Mn,~~ manganese and a p-type dopant.

2. (Currently Amended): A ferromagnetic p-type single-crystal zinc oxide material including a ~~transition metal element consisting of Mn~~ manganese, a p-type dopant, and an n-type dopant.

3. (Currently Amended): A method for manufacturing a ferromagnetic p-type single-crystal zinc oxide material as defined in claim 1, in which ~~when~~ an atomic gas from a solid-state source of Zn or Zn oxide and an activated oxygen are supplied onto a semiconductor substrate to grow a single-crystal zinc-oxide thin film on the substrate[[,]] while an atomic p-type dopant and an atomic Mn are supplied all together onto the substrate.

4. (Currently Amended): A method as defined in claim 3 for manufacturing a ferromagnetic p-type single crystal zinc oxide material including a ~~transition metal element consisting of Mn~~ manganese, a p-type

U.S. Patent Application Serial No. **10/049,615**

Amendment dated August 12, 2003

Reply to OA of **March 20, 2003**

dopant, and an n-type dopant, in which the n-type dopant is doped so as to provide a higher concentration of the p-type dopant than that of the n-type dopant.